ASZD008065D88

650V,8A Silicon Carbide Schottky Diode

Features

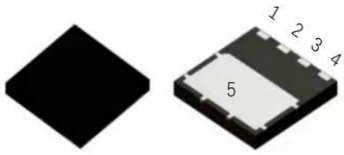
- Low reverse current
- Good surge current capability
- Low capacitive charge
- No reverse recovery current
- Compliant to Halogen-free

V_{RRM}	=	650	V
I_F (T_C=160℃)	=	8	A
Q_C	=	23	nC

Benefits

- System efficiency improvement over Si diodes
- Higher switching frequency
- Increased power density
- Essentially no switching losses

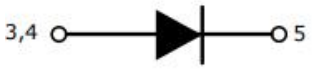
Package



DFN8*8

Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- On Board Charger
- UPS



Package Pin Definitions

- Pin1,2 - N/C
- Pin3,4 - Cathode
- Pin5 - Anode

Part Number	Package	Marking
ASZD008065D88	DFN8*8	ASZD008065D88

Maximum Ratings(T_C =25℃,unless other wise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive peak reverse voltage		650	V
V_{RSM}	Non-repetitive peak reverse voltage		650	V
I_F	Continuous forward current	T_C=25°C T_C=135°C T_C=160°C	30 15 8	A
I_{FRM}	Repetitive forward surge current	T_C=25°C , t_p=10ms, Half Sine Pulse T_C=110°C , t_p=10ms, Half Sine Pulse	35 20	A
I_{FSM}	Non-Repetitive forward surge current	T_C=25°C , t_p=10ms, Half Sine Pulse T_C=110°C , t_p=10ms, Half Sine Pulse	55 45	A
$\int i^2dt$	i^2t value	T_C=25°C , t_p=10ms, Half Sine Pulse T_C=110°C , t_p=10ms, Half Sine Pulse	15 10	A^2S
P_{tot}	Power dissipation	T_C=25°C T_C=110°C	93 40	W
T_j	Operating junction temperature		-55~175	°C
T_{stg}	Storage temperature		-55~150	°C

ElectricalCharacteristics(T_j=25℃,unless other wise specified)

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{DC}	DC blocking voltage	T_j=25°C	650			V
V_F	Diode forward voltage	I_F=8A T_j=25°C I_F=8A T_j=175°C		1.3 1.55	1.5	V
I_R	Reverse current	V_R=650V T_j=25°C V_R=650V T_j=175°C			50 200	μA
Q_C	Total capactive charge	V_R=400V T_j=25°C $Q_C = \int_0^{VR} C(V)dV$		23		nC
C	Total capacitance	V_R=0V f=1MHz V_R=200V f=1MHz V_R=400V f=1MHz		466 47 38		pF

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		1.6		°C/W

Typical Performance

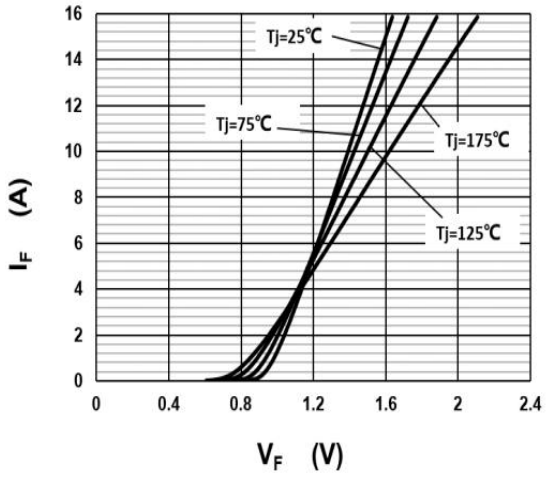


Figure 1. Typical forward characteristics

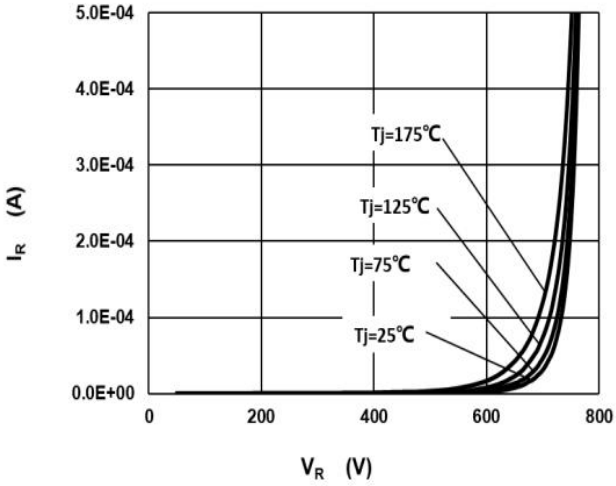


Figure 2. Typical reverse current as function of reverse voltage

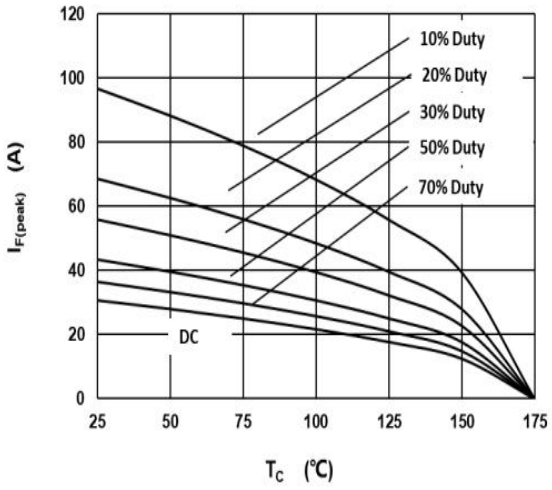


Figure 3. Diode forward current as function of temperature, D=duty cycle

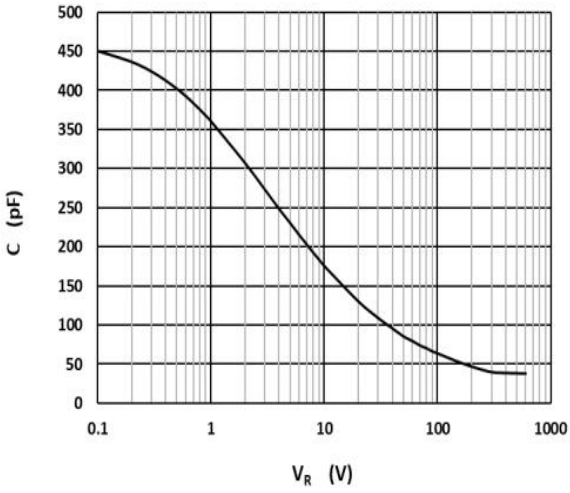


Figure 4. Typical capacitance as function of reverse voltage, C=f(V_R); T_j=25°C

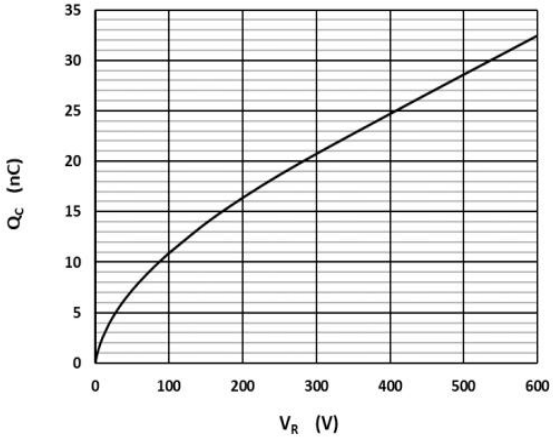


Figure 5. Typical reverse charge as function of reverse voltage

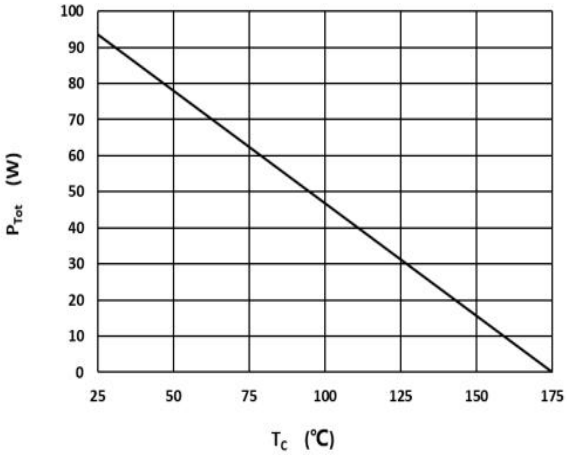


Figure 6. Power dissipation as function of case temperature

Typical Performance

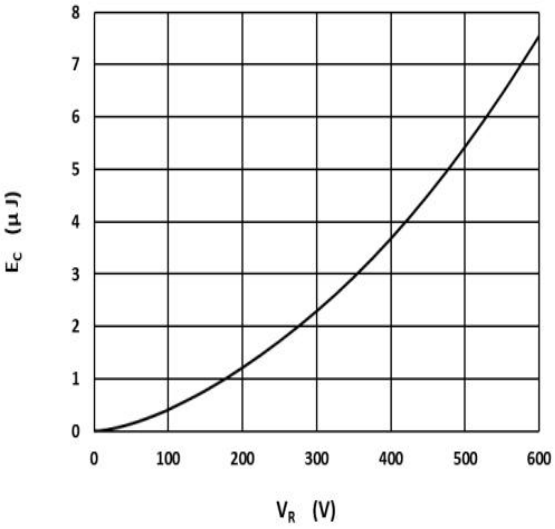


Figure 7.Capacitance stored energy

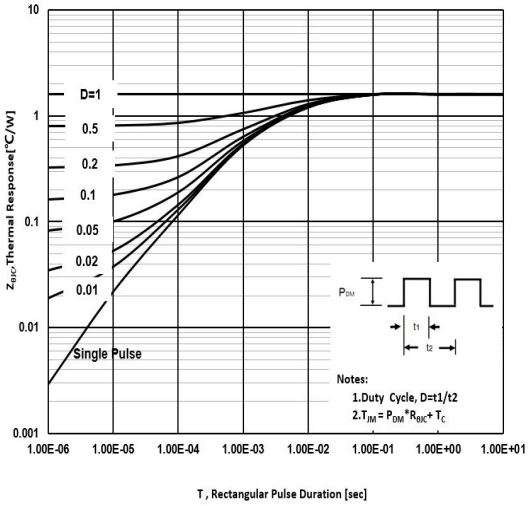
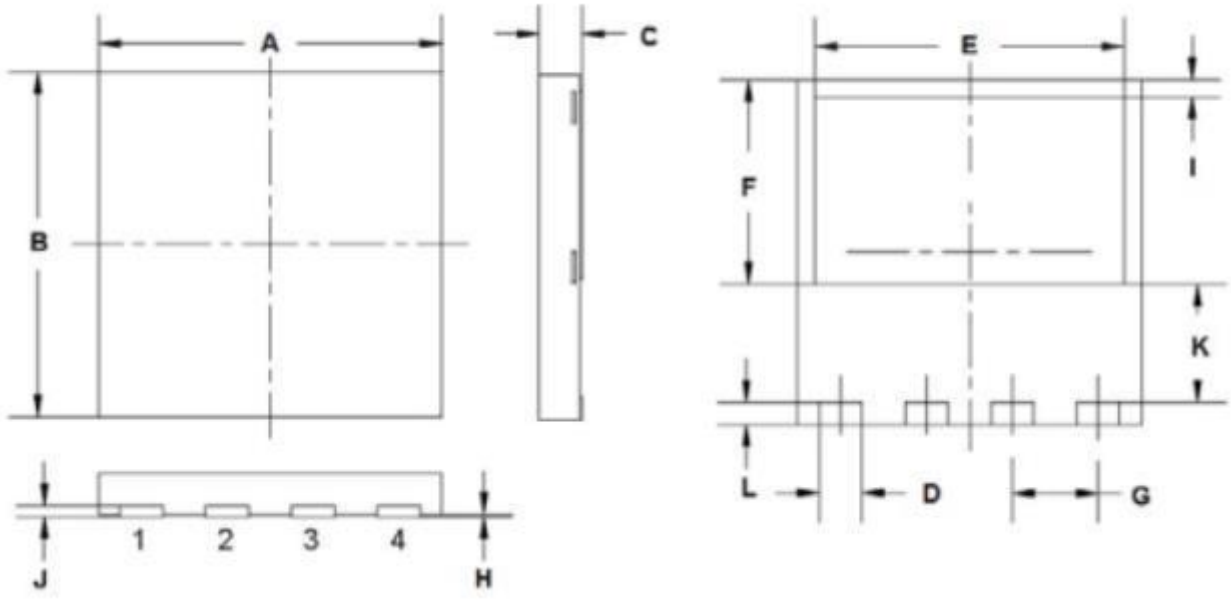


Figure 8. Max. transient thermal impedance

Package Dimensions



Dimension	Min.	Max.
A	7.90	8.10
B	7.90	8.10
C	0.75	0.95
D	0.90	1.10
E	7.10	7.30
F	4.65	4.85
G	1.80	2.20
H	0.00	0.05
I	0.30	0.50
J	0.10	0.30
K	2.65	2.85
L	0.40	0.60